

TRANSISTORS, POWER, MOSFET, N-CHANNEL, BASED ON TYPE BUY **CS***				319G
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000 Detail ESCC	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Aug 2012
		Remarks These devices have a TID tested capability of 100 kRad (Si) SEE tested : LET (MeV-cm ² /mg) 56 @ V _{GS} = -10V, V _{DS} = 250V SOA and SE SOA derating graphs are incorporated in the Detail Specifications.		
5205/026, 5205/027, 5205/030				
Qualified range: 5205/026 — variants 01R, 02R, 03R, 04R 5205/027 — variant 01R, 02R 5205/030 — variants 01R, 02R, 03R, 04R, 05R, 06R				

TRANSISTORS, POWER, MOSFET, N-CHANNEL, RADHARD BASED ON TYPE BUY 15CS				339E
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000 Detail ESCC 5205/031	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	May 2016
		Remarks		
Qualified range:				
Variant Number	Based on Type			
01	BUY15CS23J-01			
02	BUY15CS57A-01			
03	BUY15CS23K-01			
04	BUY15CS45B-01			
05	BUY15CS23J-02			
06	BUY15CS57A-02			
07	BUY15CS23K-02			
08	BUY15CS45B-02			
Variant 01, 02, 03, 04: 8 inch wafer process. Variant 05, 06, 07, 08: 12 inch wafer process.				
These devices have a TID tested capability of 100 kRad (Si) SEE tested : LET (MeV-cm²/mg) 56 @ V _{GS} = -10V, V _{DS} = 250V SOA and SE SOA derating graphs are incorporated in the Detail Specifications.				
Operating Temperature Range (°C): Top = - 55 to +150				

TRANSISTORS, POWER, MOSFET, N-CHANNEL, RADHARD BASED ON TYPE BUY 06CS				363C																		
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date																		
Generic ESCC 5000 Detail ESCC 5205/032	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	January 2020																		
Remarks																						
Qualified range:																						
<table><tr><td>Variant Number</td><td>Based on Type</td></tr><tr><td>01</td><td>BUY06CS35J-01</td></tr><tr><td>02</td><td>BUY06CS80A-01</td></tr><tr><td>03</td><td>BUY06CS23K-01</td></tr><tr><td>04</td><td>BUY06CS45B-01</td></tr><tr><td>05</td><td>BUY06CS35J-02</td></tr><tr><td>06</td><td>BUY06CS80A-02</td></tr><tr><td>07</td><td>BUY06CS23K-02</td></tr><tr><td>08</td><td>BUY06CS45B-02</td></tr></table>					Variant Number	Based on Type	01	BUY06CS35J-01	02	BUY06CS80A-01	03	BUY06CS23K-01	04	BUY06CS45B-01	05	BUY06CS35J-02	06	BUY06CS80A-02	07	BUY06CS23K-02	08	BUY06CS45B-02
Variant Number	Based on Type																					
01	BUY06CS35J-01																					
02	BUY06CS80A-01																					
03	BUY06CS23K-01																					
04	BUY06CS45B-01																					
05	BUY06CS35J-02																					
06	BUY06CS80A-02																					
07	BUY06CS23K-02																					
08	BUY06CS45B-02																					
Variant 01, 02, 03, 04: 8 inch wafer process. Variant 05, 06, 07, 08: 12 inch wafer process.																						
These devices have a TID tested capability of 100 kRad (Si) SOA derating graphs are incorporated in the Detail Specification.																						
Operating Temperature Range (°C): Top = - 55 to +150																						

TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPES BUY65CS08J-01, BUY65CS28A-01				360C
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	May 2020
Detail ESCC 5205/033		Remarks		
Qualified range:				
Variant Number	Based on Type			
01	BUY65CS08J-01			
02	BUY65CS28A-01			
03	BUY65CS08J-02			
04	BUY65CS28A-02			
Variant 01, 02: 8 inch wafer process. Variant 03, 04: 12 inch wafer process.				
Operating Temperature Range (°C): Top = - 55 to +150				

6.12.4 RF/Microwave, NPN, Low Power, Low Noise

TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPE BFY 193				230M
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5010 Detail ESCC 5611/006	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Jun 1996
		Remarks		
Qualified range:				
Variants 03 to 09				
Characteristics for BFY 193:				
V _{CEO} (V) max.		12		
V _{CBO} (V)max.		20		
h _{FE} min/max.		50/175	@ VCE = 8.0 V, IC = 30mA	
NF (dB) max.	@ 2 GHz	2.9	@ VCE = 5.0 V, IC = 15mA	
MAG/MSG (dB) min.	@ 2 GHz	12.5	@ VCE = 5.0 V, IC = 40mA	
f _T (GHz) min.	@ 500 MHz	6.5	@ VCE = 5.0 V, IC = 40mA	
Package: “ Micro-X1”				
Total Power Dissipation (P _{tot}) = 580 mW				
Operating Temperature Range (°C): Top = - 65 to +200				

TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPE BFY 450				245M
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5010 Detail ESCC 5611/008	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Jun 1997
Remarks				
Qualified range: Variants 01, 02 and 03 are qualified. 				

TRANSISTORS, MICROWAVE, SMALL SIGNAL, BIPOLAR, BASED ON TYPES BFY 640, 640B, 650B and 740B				322G
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5010 Detail ESCC	Infineon Technologies AG Neubiberg Germany	Qualification	DLR	Jun 1997
Remarks This certificate, from its issue B, release in May 2016, includes in its scope of qualification some devices previously listed in the QPL under certificates No. 320 and 321, which are no longer maintained.				
5611/009, 5611/010, 5611/011				
Qualified range: 5611/009: variants 01, 02, 03 5611/010: variants 03, 04, 05 5611/011: variant 01, 02				